

# Medium Power Transistor (32V, 2A)

## 2SD1766 / 2SD1758 / 2SD1862

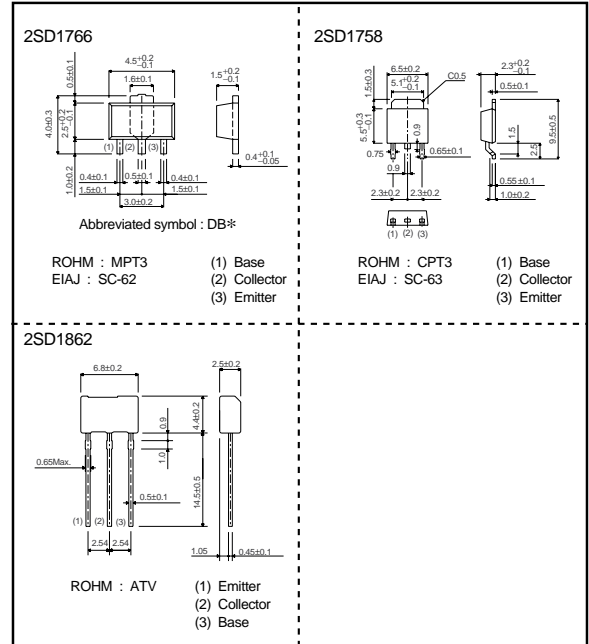
**●Features**

- 1) Low  $V_{CE(sat)}$ .  
 $V_{CE(sat)} = 0.5V(Typ.)$   
 $(I_c / I_B = 2A / 0.2A)$
- 2) Complements the 2SB1188 / 2SB1182 / 2SB1240.

**●Structure**

Epitaxial planar type  
 NPN silicon transistor

**●External dimensions (Unit : mm)**



\* Denotes hFE

**●Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CBO}$	40	V
Collector-emitter voltage	$V_{CEO}$	32	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_c$	2	A (DC)
	$I_{cP}$	2.5	A (Pulse) *1
Collector power dissipation	2SD1766	0.5	W
		2 *2	W
	2SD1758	1	W
		10	W (Tc=25°C)
2SD1862	1 *3	W	
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

\*1 Single pulse, Pw=20ms  
 \*2 When mounted on a 40x40x0.7 mm ceramic board.  
 \*3 Printed circuit board: 1.7 mm thick, collector copper plating 1 cm<sup>2</sup> or larger.

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	
Collector-base breakdown voltage	BV <sub>CB0</sub>	40	–	–	V	I <sub>c</sub> =50μA	
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	32	–	–	V	I <sub>c</sub> =1mA	
Emitter-base breakdown voltage	BV <sub>EBO</sub>	5	–	–	V	I <sub>E</sub> =50μA	
Collector cutoff current	I <sub>CB0</sub>	–	–	1	μA	V <sub>CB</sub> =20V	
Emitter cutoff current	I <sub>EBO</sub>	–	–	1	μA	V <sub>EB</sub> =4V	
DC current transfer ratio	2SD1766,2SD1758,	h <sub>FE</sub>	82	–	390	–	V <sub>CE</sub> =3V, I <sub>c</sub> =0.5A
	2SD1862		120	–	390		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	–	0.5	0.8	V	I <sub>c</sub> /I <sub>B</sub> =2A/0.2A	
Transition frequency	f <sub>T</sub>	–	100	–	MHz	V <sub>CE</sub> =5V, I <sub>E</sub> =–500mA, f=100MHz	
Output capacitance	C <sub>ob</sub>	–	30	–	pF	V <sub>CB</sub> =10V, I <sub>E</sub> =0A, f=1MHz	

\* Measured using pulse current.

●Packaging specifications and h<sub>FE</sub>

Type	h <sub>FE</sub>	Package	Taping		
		Code Basic ordering unit (pieces)	T100	TL	TV2
2SD1766	PQR	○	–	–	–
2SD1758	PQR	–	○	–	–
2SD1862	QR	–	–	–	○

h<sub>FE</sub> values are classified as follows :

Item	P	Q	R
h <sub>FE</sub>	82 to 180	120 to 270	180 to 390

●Electrical characteristic curves

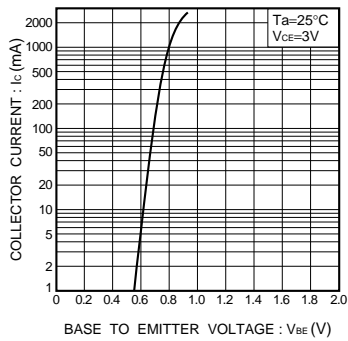


Fig.1 Grounded emitter propagation characteristics

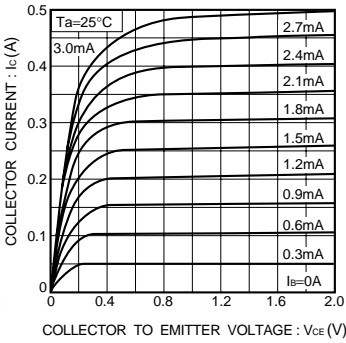


Fig.2 Grounded emitter output characteristics

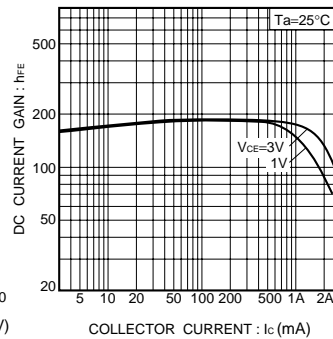


Fig.3 DC current gain vs. collector current

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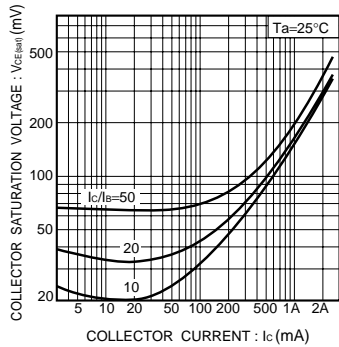


Fig.4 Collector-emitter saturation voltage vs. collector current

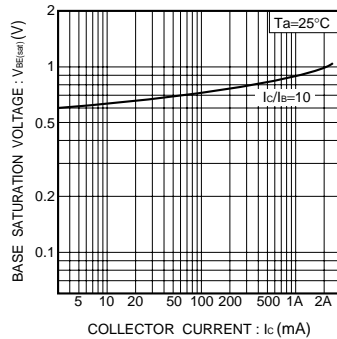


Fig.5 Collector-emitter saturation voltage vs. collector current

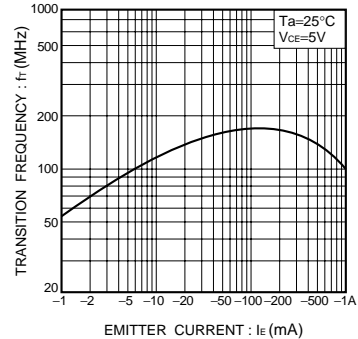


Fig.6 Transition frequency vs. emitter current

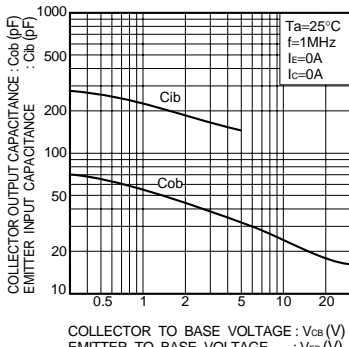


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

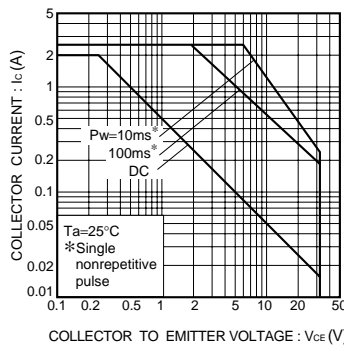


Fig.8 Safe operating area (2SD1766)

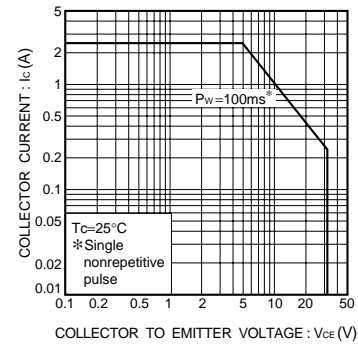


Fig.9 Safe operating area (2SD1758)

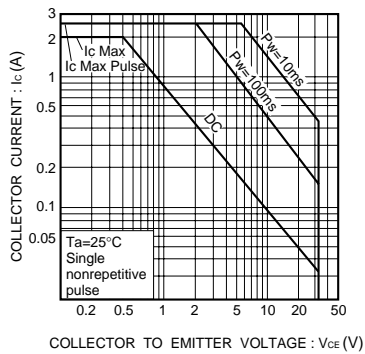


Fig.10 Safe operating area (2SD1862)

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